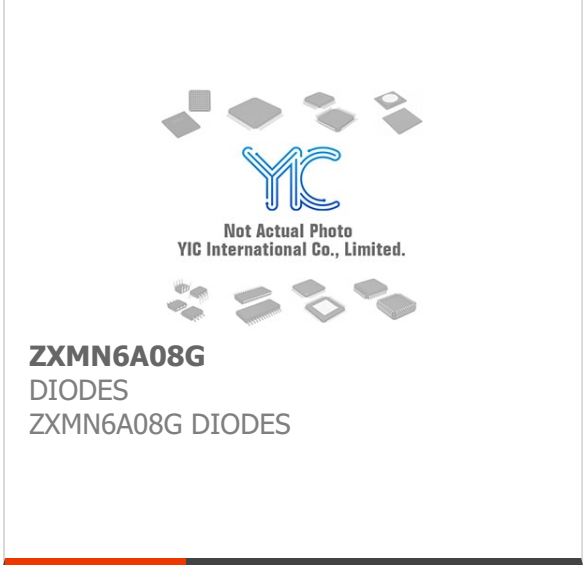
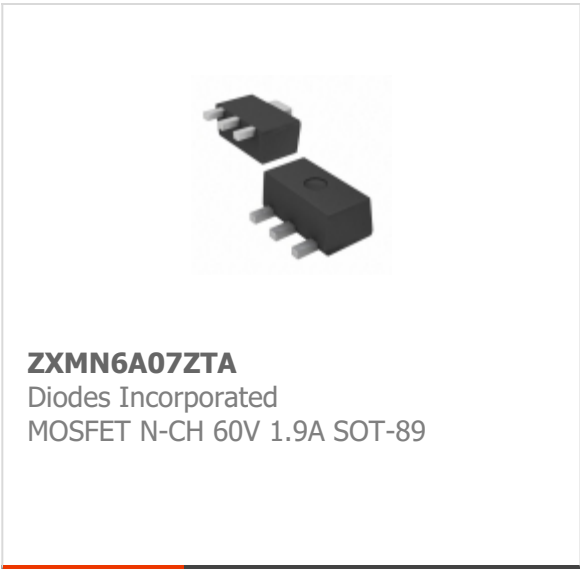
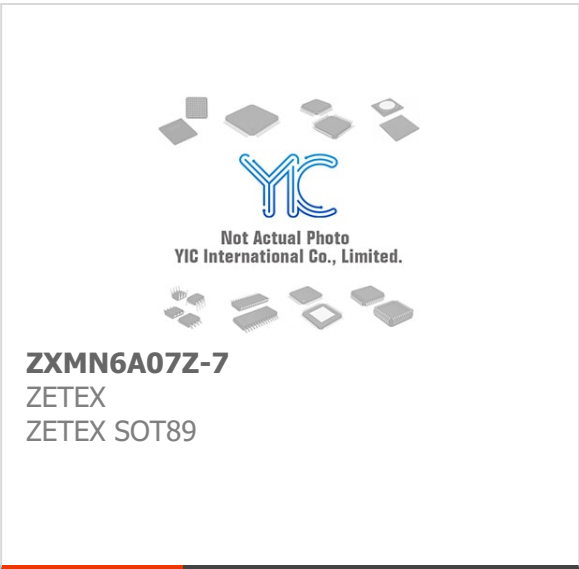


Specifications	
Part Number	ZXMN6A08E6TA
Manufacturer	Diodes Incorporated
Description	MOSFET N-CH 60V 2.8A SOT23-6
Category	Discrete Semiconductor Products > Transistors - FETs,
Part Status	216173 pcs Stock
Series	-
Technology	MOSFET (Metal Oxide)
Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type	Surface Mount
Package / Case	SOT-23-6
Supplier Device Package	SOT-26
Power Dissipation (Max)	1.1W (Ta)
FET Type	N-Channel
FET Feature	-
Drain to Source Voltage (Vdss)	60V
Current - Continuous Drain (Id) @ 25°C	2.8A (Ta)
Rds On (Max) @ Id, Vgs	80 mOhm @ 4.8A, 10V
Vgs(th) (Max) @ Id	1V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	5.8nC @ 10V
Input Capacitance (Ciss) (Max) @ Vds	459pF @ 40V
Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Vgs (Max)	±20V
Packaging	Tape & Reel (TR)

In:

ZXMN6A08GQTA
Diodes Incorporated
MOSFET N-CH 60VSOT223



More

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